



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

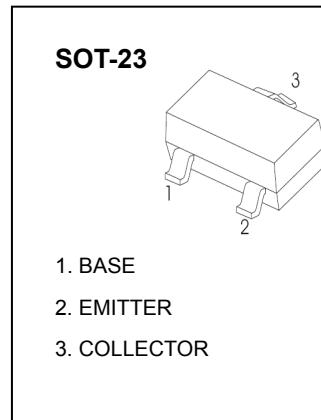
SOT-23 Plastic-Encapsulate Transistors

MMBT2907

TRANSISTOR (PNP)

FEATURES

- Epitaxial planar die construction
- Complementary NPN Type available(MMBT2222)

Marking: M2B**MAXIMUM RATINGS (T_a=25°C unless otherwise noted)**

| Symbol | Parameter | Value | Unit |
|------------------|--|-------------|------|
| V _{CBO} | Collector-Base Voltage | -60 | V |
| V _{CEO} | Collector-Emitter Voltage | -40 | V |
| V _{EBO} | Emitter-Base Voltage | -5 | V |
| I _c | Collector Current -Continuous | -600 | mA |
| P _D | Total Device Dissipation | 250 | mW |
| R _{θJA} | Thermal Resistance Junction to Ambient | 500 | °C/W |
| T _J | Junction Temperature | 150 | °C |
| T _{stg} | Storage Temperature | -55 to +150 | °C |

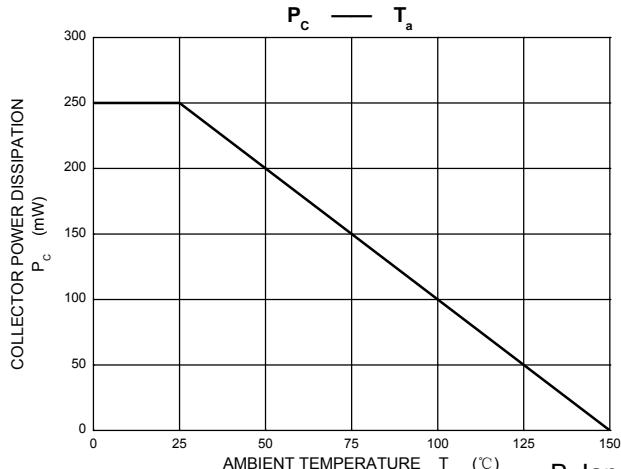
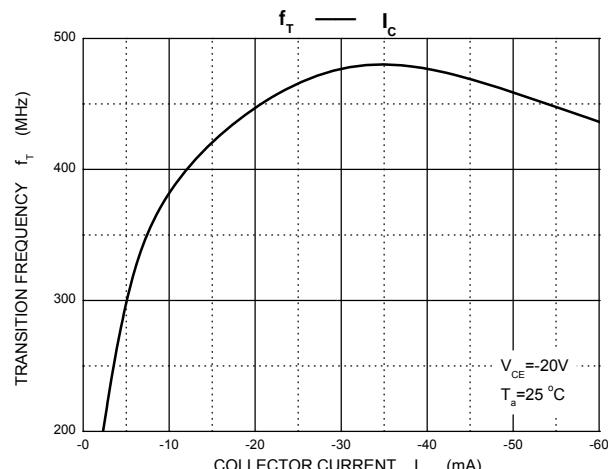
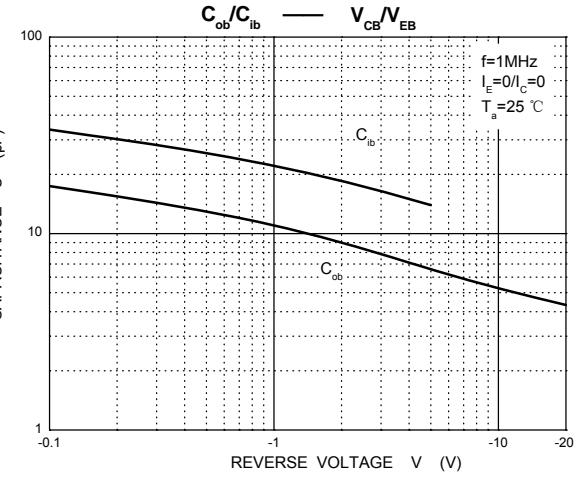
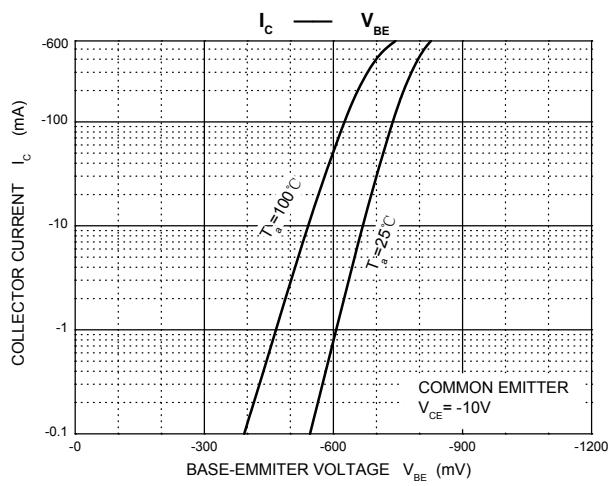
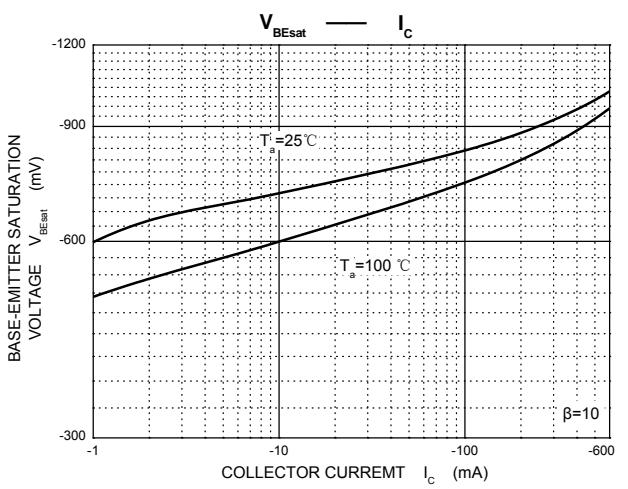
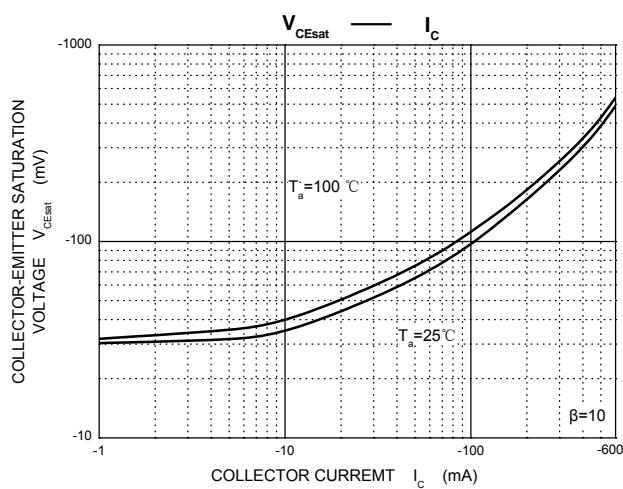
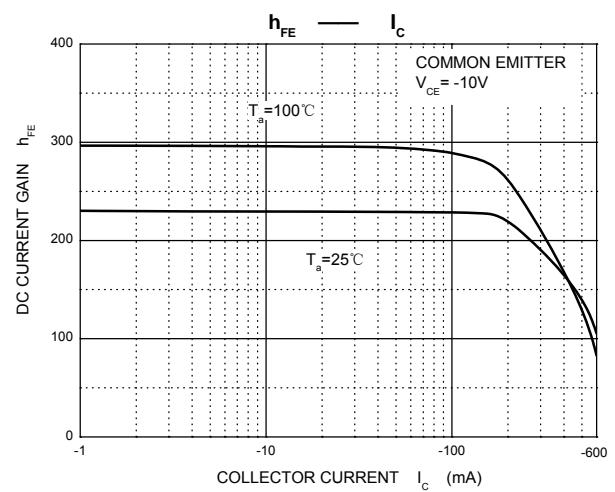
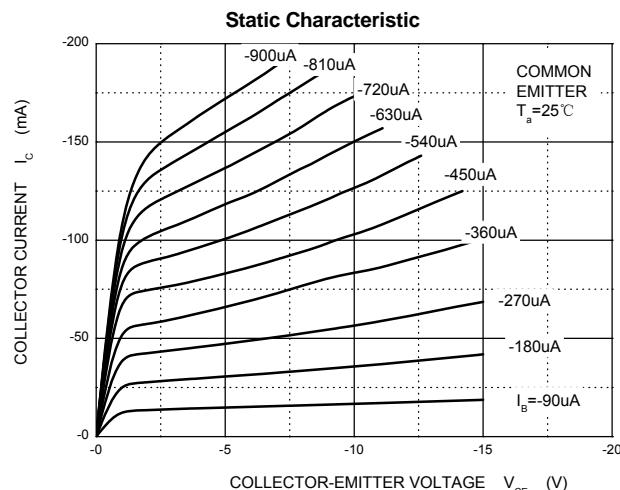
ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

| Parameter | Symbol | Test conditions | Min | Typ | Max | Unit |
|--------------------------------------|-----------------------|---|-----|-----|-------|------|
| Collector-base breakdown voltage | V _{(BR)CBO} | I _C =-10μA, I _E =0 | -60 | | | V |
| Collector-emitter breakdown voltage | V _{(BR)CEO*} | I _C =-10mA, I _B =0 | -40 | | | V |
| Emitter-base breakdown voltage | V _{(BR)EBO} | I _E =-10μA, I _C =0 | -5 | | | V |
| Collector cut-off current | I _{CBO} | V _{CB} =-50V, I _E =0 | | | -20 | nA |
| Base cut-off current | I _{EBO} | V _{CE} =-3V, I _C =0 | | | -10 | nA |
| Collector cut-off current | I _{CEX} | V _{CE} =-30 V, V _{BE(off)} =-0.5V | | | -50 | nA |
| DC current gain | h _{FE(1)*} | V _{CE} =-10V, I _C =-150mA | 100 | | 300 | |
| | h _{FE(2)*} | V _{CE} =-10V, I _C =-0.1mA | 52 | | | |
| | h _{FE(3)*} | V _{CE} =-10V, I _C =-500mA | 32 | | | |
| Collector-emitter saturation voltage | V _{CE(sat)*} | I _C =-150mA, I _B =-15mA | | | -0.4 | V |
| | V _{CE(sat)*} | I _C =-500mA, I _B =-50mA | | | -0.67 | V |
| Base-emitter saturation voltage | V _{BE(sat)*} | I _C =-150mA, I _B =-15mA | | | -1 | V |
| | V _{BE(sat)*} | I _C =-500mA, I _B =-50mA | | | -1.2 | V |
| Transition frequency | f _T | V _{CE} =-20V, I _C =-50mA, f=100MHz | 200 | | | MHz |
| Delay time | t _d | V _{CE} =-30V, I _C =-150mA, I _{B1} =-15mA | | | 10 | ns |
| Rise time | t _r | | | | 25 | ns |
| Storage time | t _s | | | | 225 | ns |
| Fall time | t _f | I _C =-6V, I _C =-150mA, I _{B1} =- I _{B2} =- 15mA | | | 60 | ns |

*Pulse test: t_p≤300μs, δ≤0.02.

Typical Characteristics

MMBT2907



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